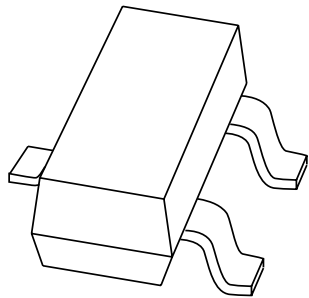


DATA SHEET



PMBD6100 High-speed double diode

Product specification
Supersedes data of 1999 May 11

2003 Mar 25

High-speed double diode

PMBD6100

FEATURES

- Small plastic SMD package
- High switching speed: max. 4 ns
- General application
- Continuous reverse voltage: max. 70 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 450 mA.

APPLICATIONS

- High-speed switching in surface mounted circuits.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾
PMBD6100	*5B

Note

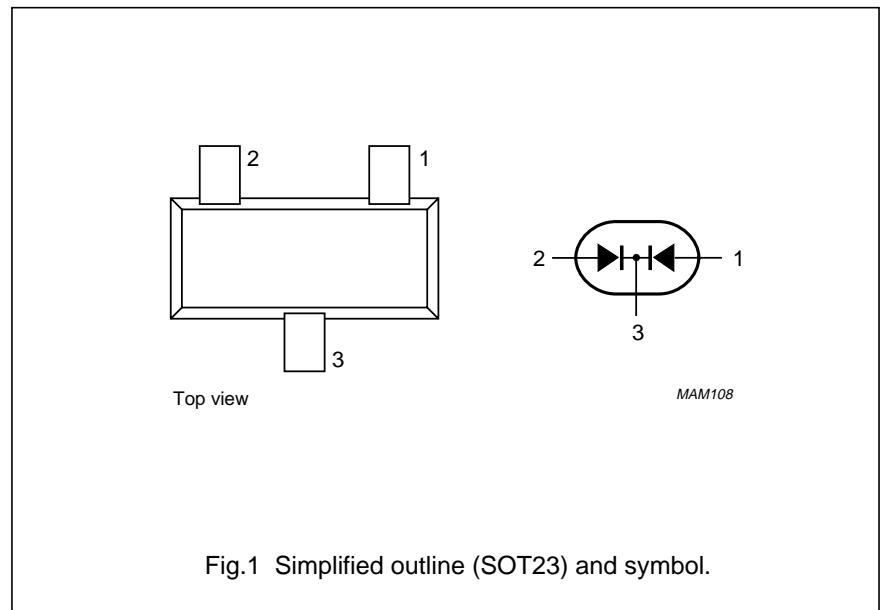
- * = p : Made in Hong Kong.
 * = t : Made in Malaysia.
 * = W : Made in China.

DESCRIPTION

The PMBD6100 consists of two high-speed switching diodes with common cathodes, fabricated in planar technology, and encapsulated in the small SOT23 plastic SMD package.

PINNING

PIN	DESCRIPTION
1	anode (a1)
2	anode (a2)
3	common cathode



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode					
V_{RRM}	repetitive peak reverse voltage		–	85	V
V_R	continuous reverse voltage		–	70	V
I_F	continuous forward current	single diode loaded; note 1; see Fig.2	–	215	mA
		double diode loaded; note 1; see Fig.2	–	125	mA

High-speed double diode

PMBD6100

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{FRM}	repetitive peak forward current		–	450	mA
I_{FSM}	non-repetitive peak forward current	square wave; $T_j = 25\text{ °C}$ prior to surge; see Fig.4 $t = 1\ \mu\text{s}$ $t = 1\ \text{ms}$ $t = 1\ \text{s}$	– – –	4 1 0.5	A A A
P_{tot}	total power dissipation	$T_{amb} = 25\text{ °C}$; note 1	–	250	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C

Note

1. Device mounted on an FR4 printed-circuit board.

ELECTRICAL CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode					
V_F	forward voltage	see Fig.3 $I_F = 1\ \text{mA}$ $I_F = 10\ \text{mA}$ $I_F = 50\ \text{mA}$ $I_F = 100\ \text{mA}$	550 – – 0.85	700 855 1 1.1	mV mV V V
I_R	reverse current	see Fig.5 $V_R = 50\ \text{V}$ $V_R = 50\ \text{V}$; $T_j = 150\text{ °C}$	– –	100 50	nA μA
C_d	diode capacitance	$f = 1\ \text{MHz}$; $V_R = 0$; see Fig.6	–	1.5	pF
t_{rr}	reverse recovery time	when switched from $I_F = 10\ \text{mA}$ to $I_R = 10\ \text{mA}$; $R_L = 100\ \Omega$; measured at $I_R = 1\ \text{mA}$; see Fig.7	–	4	ns
V_{fr}	forward recovery voltage	when switched from $I_F = 10\ \text{mA}$; $t_r = 20\ \text{ns}$; see Fig.8	–	1.75	V

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-tp}$	thermal resistance from junction to tie-point		360	K/W
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	500	K/W

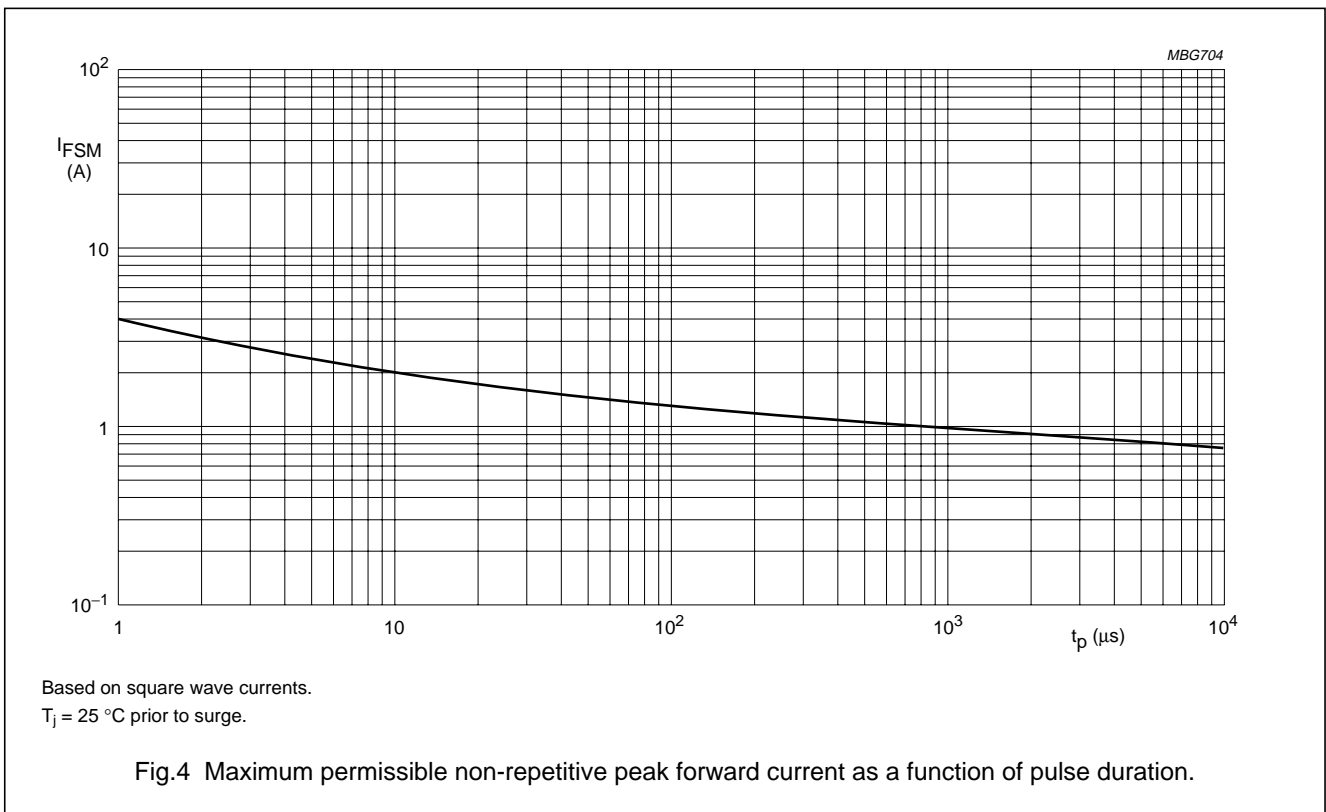
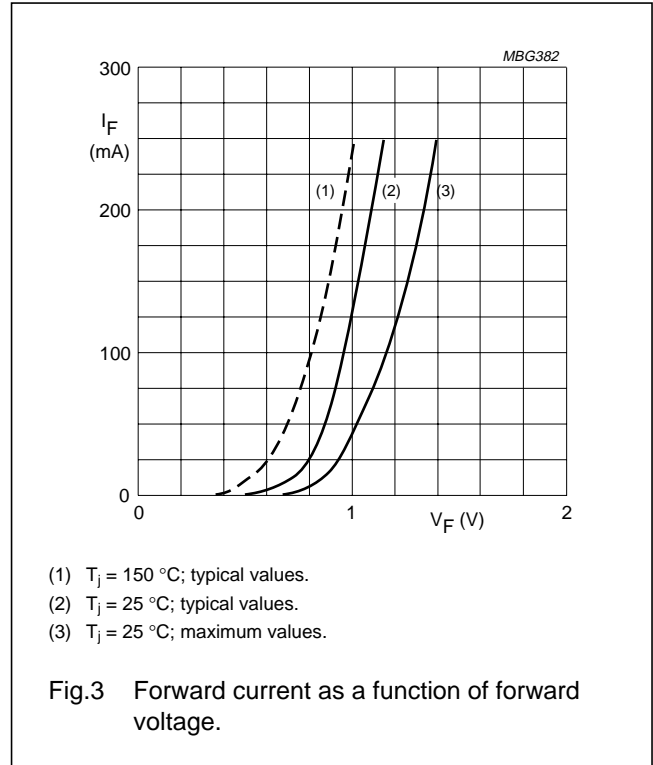
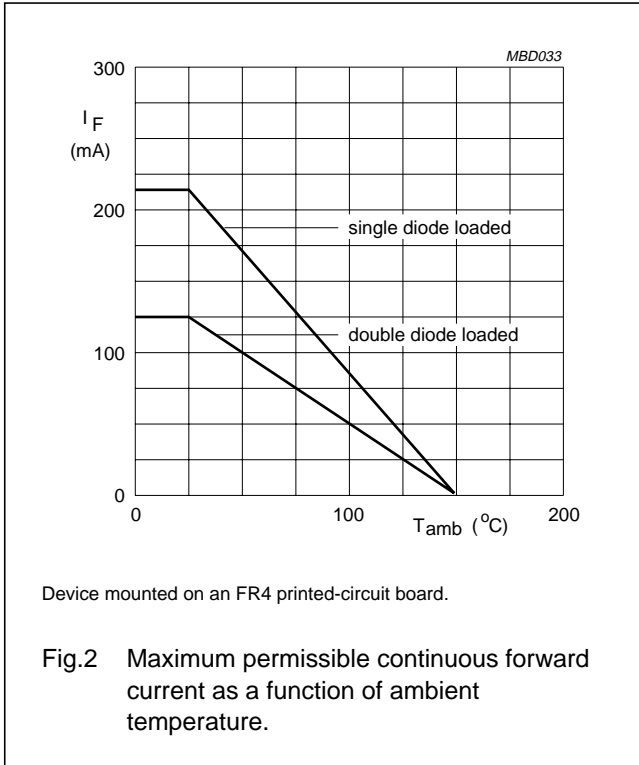
Note

1. Device mounted on an FR4 printed-circuit board.

High-speed double diode

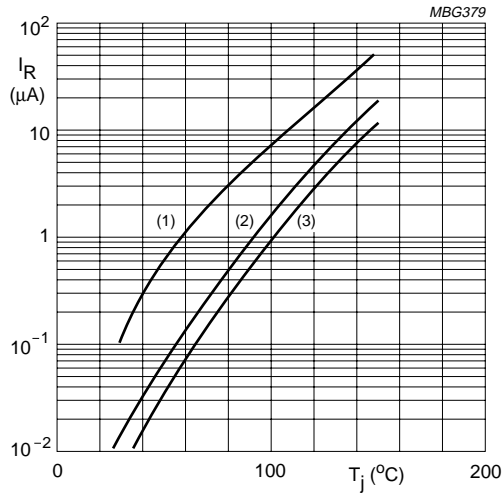
PMBD6100

GRAPHICAL DATA



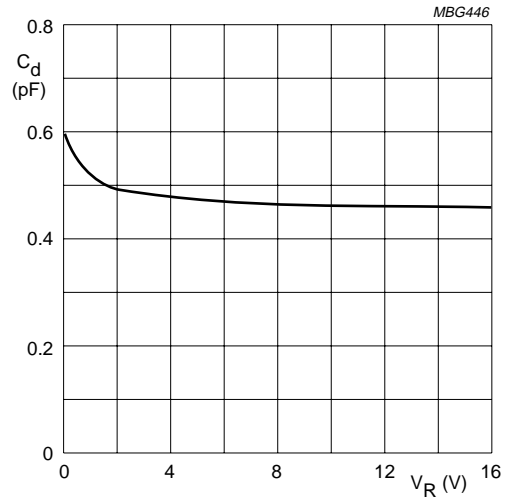
High-speed double diode

PMBD6100



- (1) $V_R = 50$ V; maximum values.
- (2) $V_R = 50$ V; typical values.
- (3) $V_R = 30$ V; typical values.

Fig.5 Reverse current as a function of junction temperature.

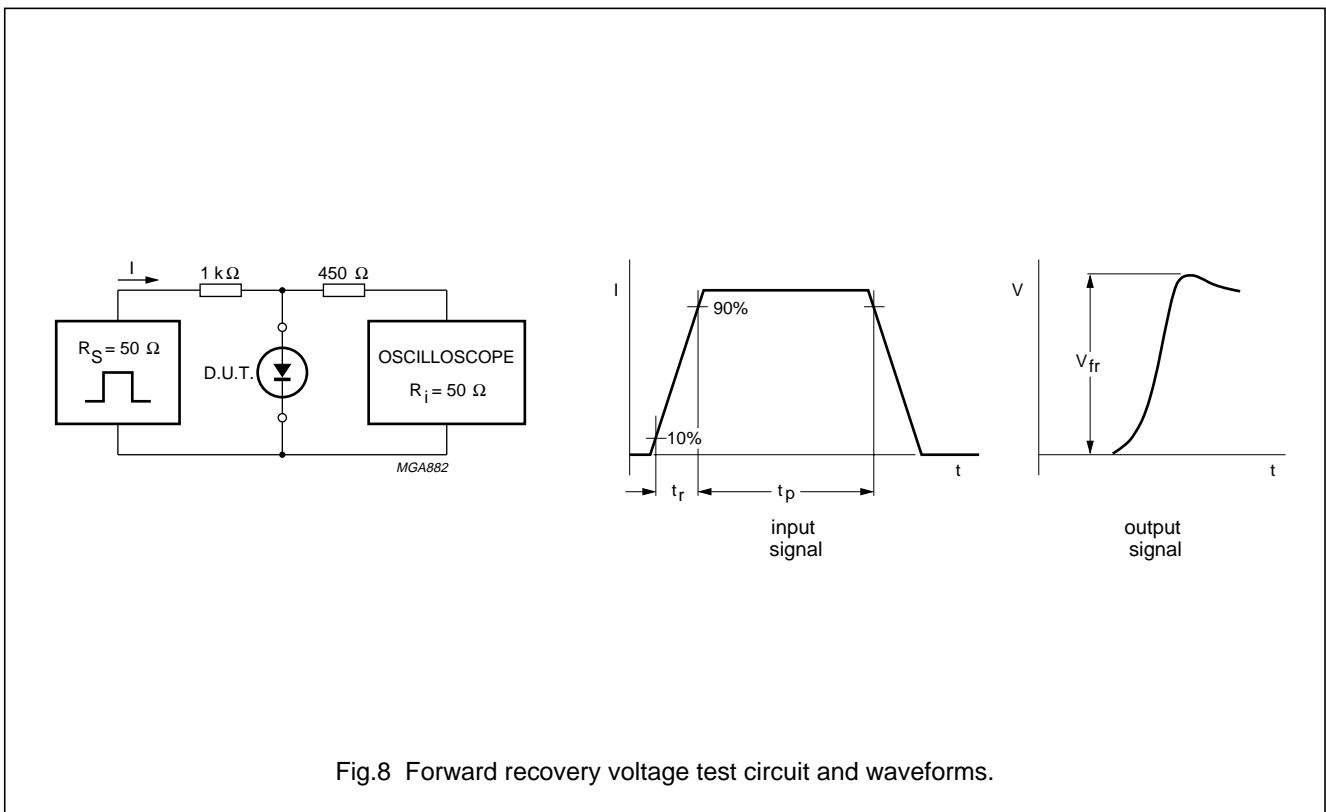
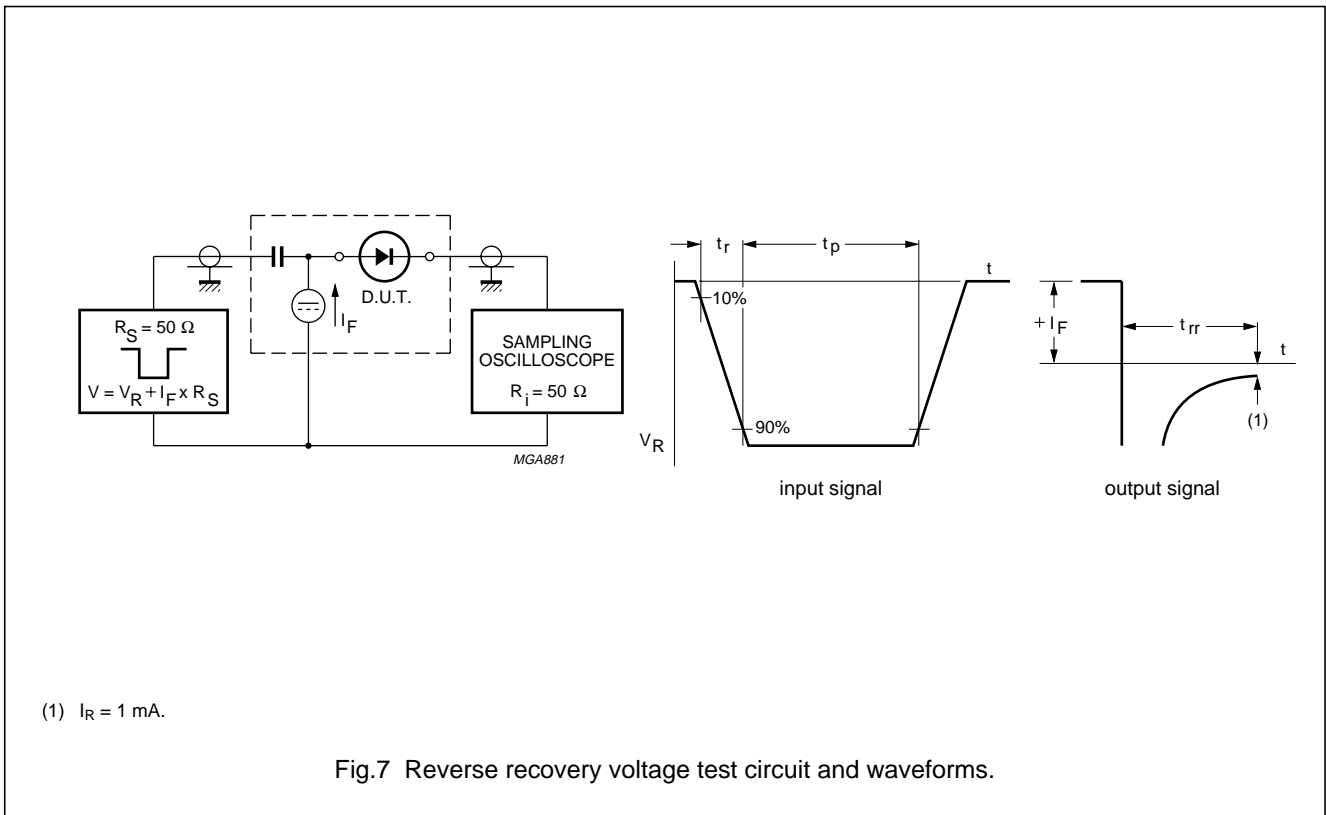


$f = 1$ MHz; $T_j = 25$ °C.

Fig.6 Diode capacitance as a function of reverse voltage; typical values.

High-speed double diode

PMBD6100



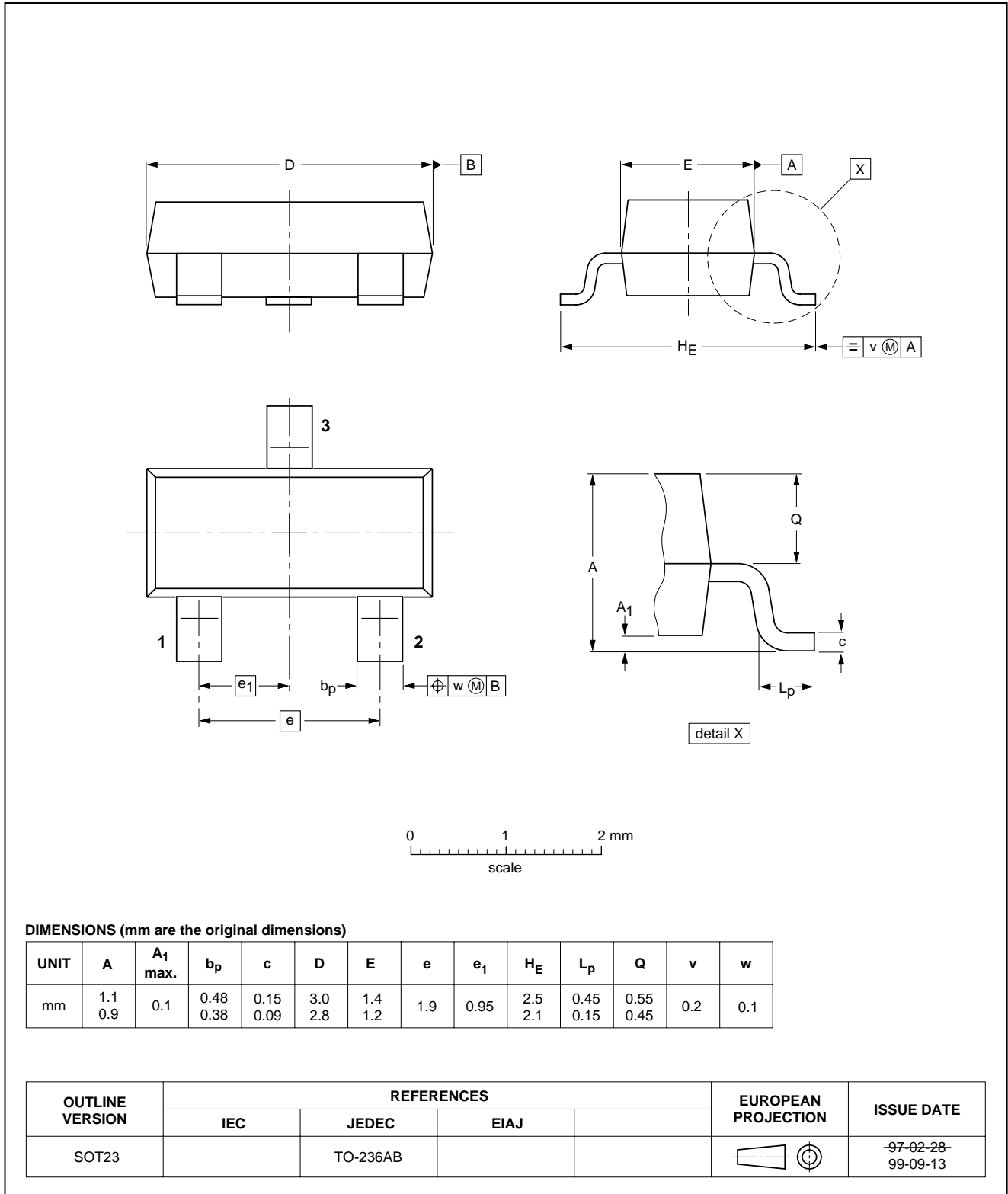
High-speed double diode

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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



High-speed double diode

PMBD6100

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
III	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

Notes

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2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.
3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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High-speed double diode

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NOTES

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NOTES

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NOTES

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